

Internally Matched Power GaAs FETs (C-Band)

Features

- High power
 - $P_{1dB} = 42.5$ dBm at 5.0 GHz to 5.3 GHz
- High gain
 - $G_{1dB} = 8$ dB at 5.0 GHz to 5.3 GHz
- Broad band internally matched
- Hermetically sealed package

RF Performance Specifications ($T_a = 25^\circ \text{C}$)

Characteristics	Symbol	Condition	Unit	Min.	Typ.	Max
Output Power at 1dB Compression Point	P_{1dB}	$V_{DS} = 10V$ $f = 5.0 \sim 5.3 \text{ GHz}$	dBm	41.5	42.5	–
Power Gain at 1dB Compression Point	G_{1dB}		dB	7.0	8.0	–
Drain Current	I_{DS}		A	–	4.8	5.5
Power Added Efficiency	η_{add}		%	–	31	–
Channel-Temperature Rise	ΔT_{ch}	$V_{DS} \times I_{DS} \times R_{th(c-c)}$	$^\circ\text{C}$	–	–	80

Electrical Characteristics ($T_a = 25^\circ \text{C}$)

Characteristic	Symbol	Condition	Unit	Min.	Typ.	Max
Trans-conductance	gm	$V_{DS} = 3V$ $I_{DS} = 6.0 \text{ A}$	mS	–	3600	–
Pinch-off Voltage	V_{GSoff}	$V_{DS} = 3V$ $I_{DS} = 80\text{mA}$	V	-2.0	-3.5	-5.0
Saturated Drain Current	I_{DSS}	$V_{DS} = 3V$ $V_{GS} = 0V$	A	–	11.6	15.0
Gate to Source Breakdown Voltage	V_{GSO}	$I_{GS} = -240 \mu\text{A}$	V	-5	–	–
Thermal Resistance	$R_{th(c-c)}$	Channel to case	$^\circ\text{C/W}$	–	1.4	1.8

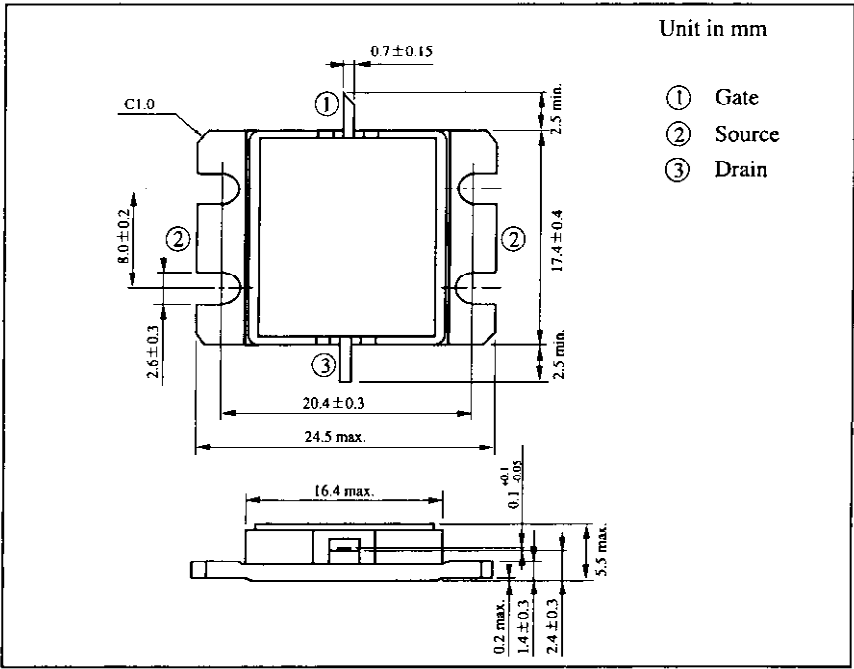
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Absolute Maximum Ratings (T_a = 25° C)

Characteristic	Symbol	Unit	Rating
Drain Source Voltage	V _{DS}	V	15
Gate Source Voltage	V _{GS}	V	-5
Drain Current	I _D	A	16
Total Power Dissipation (T _c = 25°C)	P _T	W	70
Channel Temperature	T _{ch}	°C	175
Storage Temperature	T _{stg}	°C	-65~175

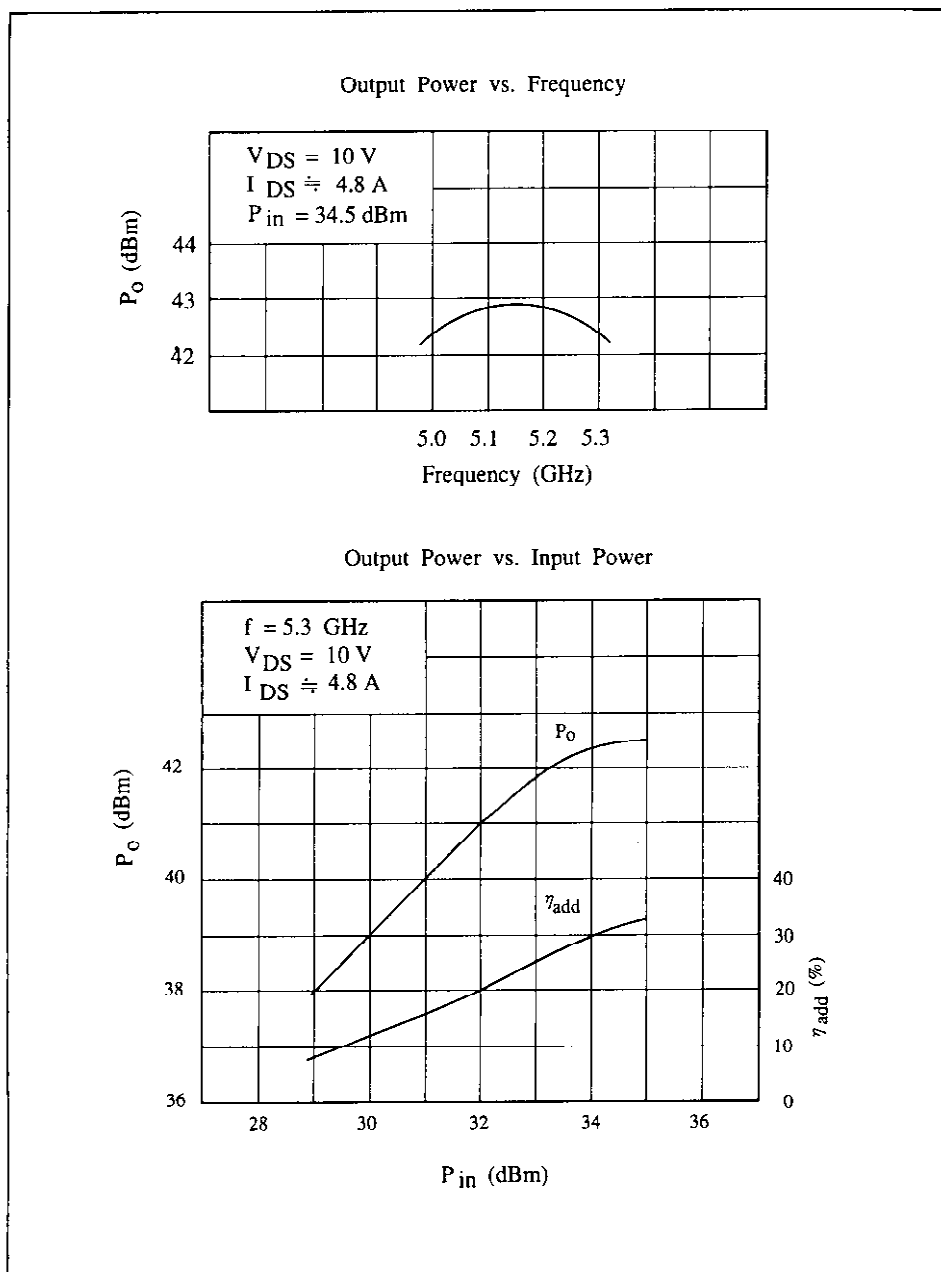
Package Outline (2-16G1B)



Handling Precautions for Packaged Type

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.

RF Performances



Power Dissipation vs. Case Temperature

